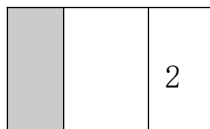
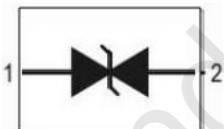




1-Line Bidirectional ESD Protection Diode

DFN1006-2L

Schematic & Pin configuration

Dimensions	Circuit Diagram
	

Device	Package	Marking	Packaging	Reel Size
ESD8LB24C	DFN1006-2L	24L	10000/Tape & Reel	7 Inch

General description

The ESD8LB24C is a bi-directional TVS diode,utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage,making this device an ideal solution for protecting voltage sensitive data and power line. The ESD8LB24C complies with the IEC 61000-4-2 (ESD)standard with $\pm 15\text{KV}$ air and $\pm 15\text{KV}$ contact discharge.It is assembled into an ultra-small 1.6x0.6x0.5mm lead-free 0402 package.The small size and high ESD surge protection make ESD8LB24C an ideal choice to protect cell phone,digital cameras,audio players and many other portable applications.

Features and benefits

- Ultra small SMD package 1.0x0.6x0.5 mm
- Bidirectional ESD protection of one line
- Femtofarad capacitance:Cj=0.5pF (Typ)
- Complies with following standards:IEC 61000-4-2 (ESD)immunity test
Air discharge: $\pm 15\text{KV}$,Contact discharge: $\pm 15\text{KV}$
- RoHS Compliant

Application information

- USB Ports
- Display Ports
- MDDI Ports
- Digital Video Interface (DVI)

Maximum Ratings (Ta=25°C, unless otherwise specified)

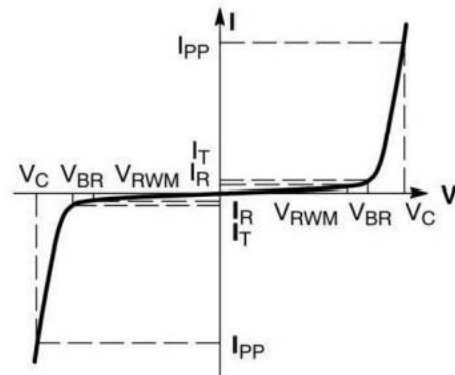
Parameter	Symbol	Value	Unit
Peak Pulse Power (Tp=8/20 μs)	PpK	40	W
Rated Peak Pulse Current (Tp=8/20 μs)	Ipp	5.0	A
Maximum lead temperature for soldering during 10s	TL	260	°C
Storage Temperature Range	Tstg	-55 to +150	°C
Operating Temperature Range	Top	-40 to +125	°C
ESD voltage IEC 61000-4-2 (air discharge)	VesD	15	kV
ESD voltage IEC 61000-4-2 (contact discharge)	VESD	15	kV

Electrical Characteristics (Ta=25°C, unless otherwise specified)

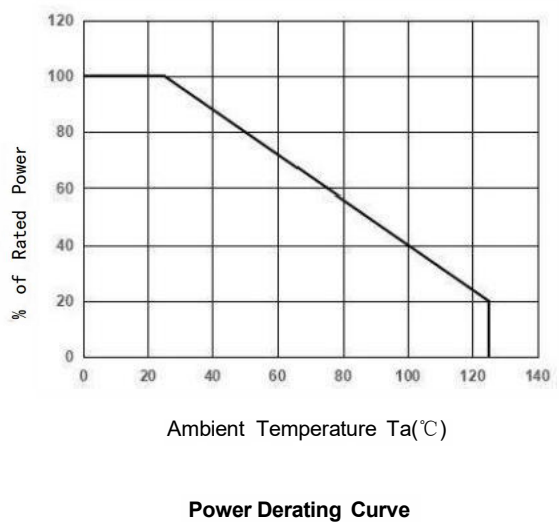
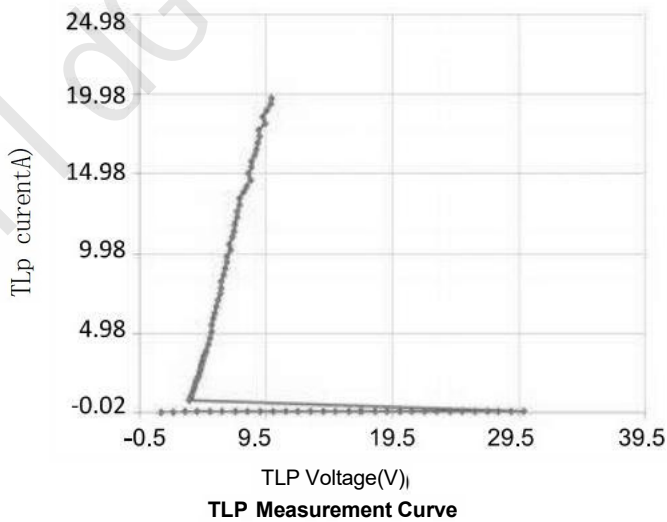
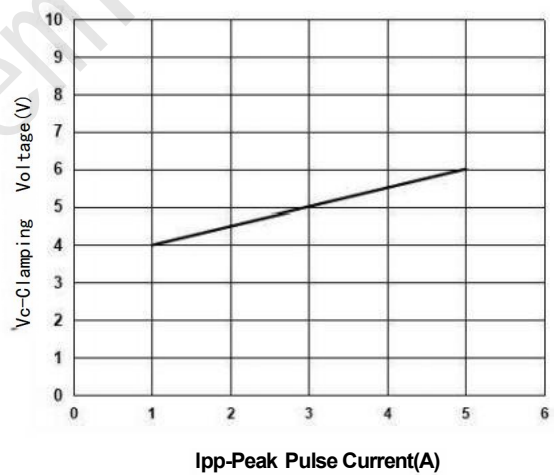
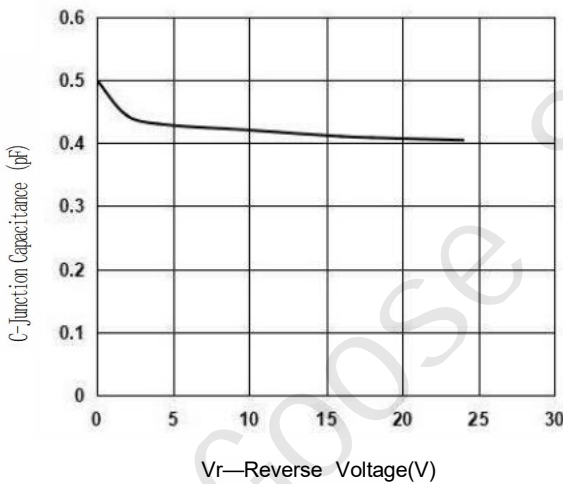
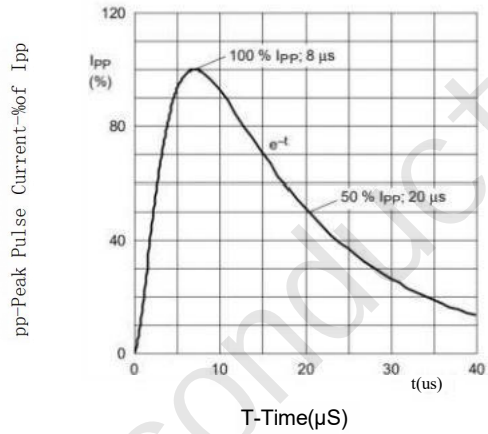
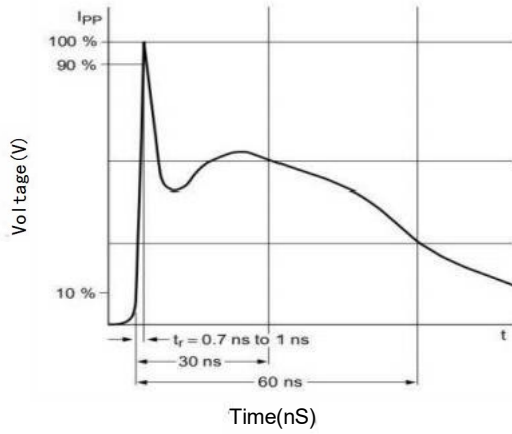
Parameter	Symbol	Min	Typ	Max	Unit	Condition
Reverse Working Voltage	VRWM			24	V	
Breakdown Voltage	VBR	26	29	32	V	Ir=1mA
Leakage Current ILeak	Ir			0.1	μA	VRwm=24V
Clamping Voltage	Vc		4.0		V	Ipp=1A, Tp=8/20 μs
Clamping Voltage	Vc		6.0	8.0	V	Ipp=5A, Tp=8/20 μs
Clamping Voltage	Vc		8.2		V	TLP =16A
Junction Capacitance	Cj		0.50	0.65	pF	VR=0V, f=1MHz

Portion Electronics Parameter

Symbol	Parameter
Ipp	Maximum Reverse Peak Pulse Current
Vc	Clamping Voltage @Ipp
VRWM	Working Peak Reverse Voltage
Ir	Maximum Reverse Leakage Current @VRWM
r	Test Current
VBR	VBR Breakdown Voltage @Ir

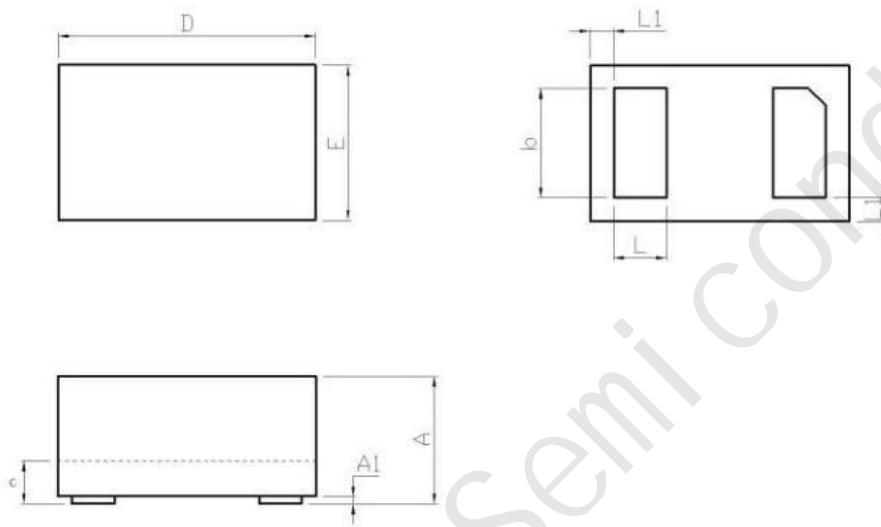


Typical Performance Characteristics (TA=25°C unless otherwise Specified)



Package Outline Dimensions

DFN1006-2L



DFN1006-2L (mm)			
Dim	Min	Typ.	Max
A	0.45	0.50	0.55
A1	0	0.02	0.05
b	0.45	0.5	0.55
C	0.1	0.15	0.18
D	0.95	1.00	1.05
E	0.55	0.60	0.65
L	0.20	0.25	0.30
L1	0.035	0.05	0.065